

Taiwan Semiconductor

25A, 35V - 150V Schottky Barrier Rectifier

FEATURES

- AEC-Q101 qualified available
- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

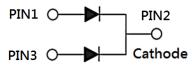
MECHANICAL DATA

- Case: ITO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N⋅m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.70g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I _F	25	А	
V _{RRM}	35 - 150	V	
I _{FSM}	200	А	
T _{J MAX}	150	°C	
Package	ITO-220AB		
Configuration	Dual dies		







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)									
		MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	
PARAMETER	SYMBOL	2535	2545	2550	2560	2590	25100	25150	UNIT
		СТ	СТ	СТ	СТ	СТ	СТ	СТ	
		MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	
Marking code on the device		2535 CT	2545 CT	2550 CT	2560 CT	2590 CT	25100 CT	25150 CT	
Repetitive peak reverse voltage	V _{RRM}	35	45	50	60	90	100	150	V
Reverse voltage, total rms value	V _{R(RMS)}	24	31	35	42	63	70	105	V
Forward current	I _F				25				Α
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I _{FSM}				200				A
Peak repetitive forward current (Rated V _R , Square wave, 20KHz)	I _{FRM}				25				А
Critical rate of rise of off-state voltage	dv/dt				10,000				V/µs
Junction temperature	T _J -55 to +150			°C					
Storage temperature	T _{STG} -55 to +150			°C					



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THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-ambient thermal resistance	R _{eja}	8	°C/W
Junction-to-case thermal resistance	R _{eJC}	1	°C/W

ELECTRICAL SPECIF	CATIONS (T _A	= 25°C unless otherwise	e noted)			
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBRF2535CT	I _F = 12.5A,T _J = 25°C		-	-	v
	MBRF2545CT					-
	MBRF2550CT			-	0.75	V
	MBRF2560CT MBRF2590CT					
	MBRF2590CT MBRF25100CT			-	0.85	V
	MBRF25150CT			-	0.95	V
	MBRF2535CT					
	MBRF2545CT			-	0.82	V
	MBRF2550CT					N
F (1)	MBRF2560CT	I _F = 25A,T _J = 25°C	VF	-	-	V
	MBRF2590CT			_	0.92	v
	MBRF25100CT			_	0.52	v
	MBRF25150CT			-	1.02	V
Forward voltage per diode ⁽¹⁾	MBRF2535CT			-	-	v
	MBRF2545CT					v
	MBRF2550CT			-	0.65	v
	MBRF2560CT	I _F = 12.5A,T _J = 125°C				•
	MBRF2590CT			-	0.75	v
	MBRF25100CT	-				
	MBRF25150CT			-	0.92	V
	MBRF2535CT			-	0.73	v
	MBRF2545CT					
	MBRF2550CT MBRF2560CT			-	-	V
	MBRF2560CT	I _F = 25A,T _J = 125°C				
	MBRF25100CT			-	0.88	V
	MBRF25150CT			-	0.98	V



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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Reverse current @ rated V _R per diode ⁽²⁾	MBRF2535CT MBRF2545CT	T _J = 25°C T _J = 125°C		_	2	mA
	MBRF2550CT MBRF2560CT				_	
	MBRF2590CT MBRF25100CT MBRF25150CT		- I _R	-	100	μA
	MBRF2535CT MBRF2545CT			-	15	mA
	MBRF2550CT MBRF2560CT			-	10	mA
	MBRF2590CT MBRF25100CT			-	7.5	mA
	MBRF25150CT			-	5	mA

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION	l	
ORDERING CODE ⁽¹⁾⁽²⁾	PACKAGE	PACKING
MBRF25xCT	ITO-220AB	50 / Tube
MBRF25xCTH	ITO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 35V(MBRF2535CT) to 150V(MBRF25150CT)

2. "H" means AEC-Q101 qualified



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

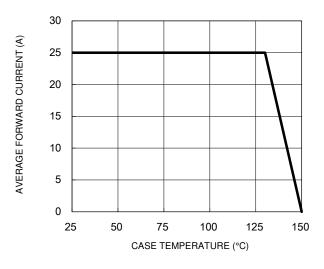


Fig.1 Forward Current Derating Curve

Fig.3 Typical Reverse Characteristics

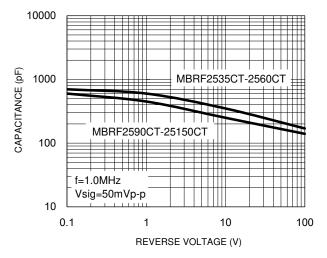
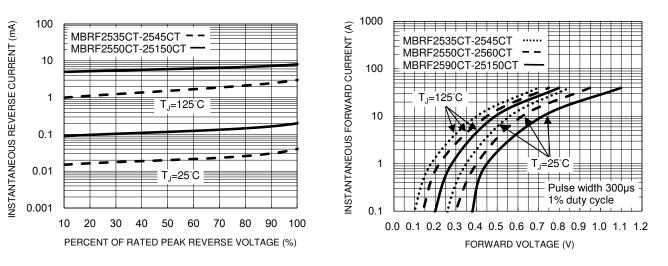


Fig.2 Typical Junction Capacitance





220 200 PEAK FORWARD SURGE CURRENT (A) 8.3ms single half sine wave 180 160 140 120 100 80 60 40 20 0 1 10 100 NUMBER OF CYCLES AT 60 Hz

Fig.5 Maximum Non-Repetitive Forward Surge Current



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

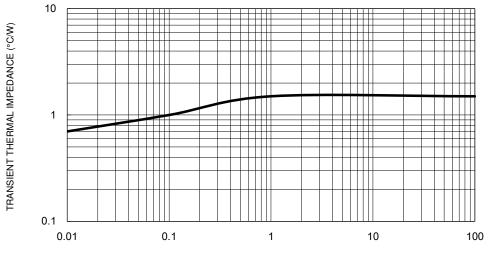


Fig.6 Typical Transient Thermal Impedance

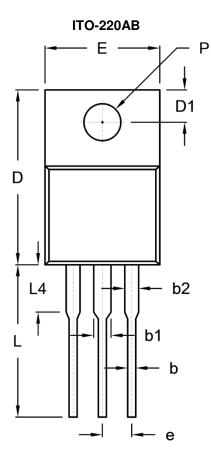
PULSE DURATION (s)

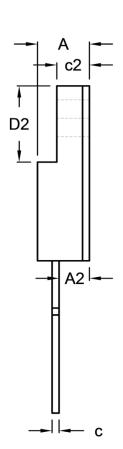


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PACKAGE OUTLINE DIMENSIONS





DIM.	Unit (mm)		Unit ((inch)	
	Min.	Max.	Min.	Max.	
A	4.30	4.70	0.169	0.185	
A2	2.30	2.96	0.091	0.117	
b	0.50	0.90	0.020	0.035	
b1	-	1.80	-	0.071	
b2	0.95	1.45	0.037	0.057	
с	0.46	0.76	0.018	0.030	
c2	2.50	3.16	0.098	0.124	
D	14.80	15.50	0.583	0.610	
D1	2.40	3.20	0.094	0.126	
D2	6.30	6.90	0.248	0.272	
E	9.60	10.30	0.378	0.406	
е	2.41	2.67	0.095	0.105	
L	12.60	13.80	0.496	0.543	
L4	-	4.10	-	0.161	
Р	3.00	3.40	0.118	0.134	

MARKING DIAGRAM

雪別 GYWWF
P/N
_+

P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



MBRF2535CT – MBRF25150CT

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